

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO263 plastic package.



## 2. Features and benefits

- High junction temperature up to 175 °C
- Low forward voltage drop, negligible switching losses
- High efficiency

## 3. Applications

- DC to DC converters
- Freewheeling diode
- OR-ing diode
- Switched mode power supply rectifier

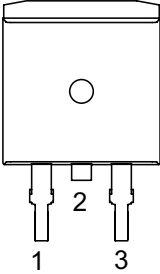
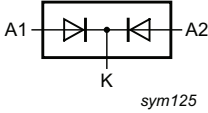
## 4. Quick reference data

Table 1. Quick reference data

| Table 1. Quick reference data |                                 |  |       |        |      |      |      |
|-------------------------------|---------------------------------|--|-------|--------|------|------|------|
| Symbol                        | Parameter                       | Conditions   | Notes | Values |      |      | Unit |
| Absolute maximum rating       |                                 |  |       |        |      |      |      |
| V <sub>RRM</sub>              | repetitive peak reverse voltage |  |       | 200    |      |      | V    |
| I <sub>F(AV)</sub>            | average forward current         | δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 148 °C; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> |       | 20     |      |      | A    |
| I <sub>O(AV)</sub>            | average output current          | δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 149 °C; both diodes conducting  |       | 40     |      |      | A    |
| Symbol                        | Parameter                       | Conditions   | Notes | Min    | Typ  | Max  | Unit |
| Static characteristics        |                                 |  |       |        |      |      |      |
| V <sub>F</sub>                | forward voltage                 | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; <a href="#">Fig. 6</a>   |       | -      | 0.87 | 0.92 | V    |
| I <sub>R</sub>                | reverse current                 | V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C; per diode; <a href="#">Fig. 7</a>  |       | -      | 0.1  | 5    | μA   |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                         | Simplified outline   | Graphic symbol   |
|-----|--------|-------------------------------------|--|--|
| 1   | A1     | anode 1                             |  | <br><i>sym125</i> |
| 2   | K      | cathode                             |  |  |
| 3   | A2     | anode 2                             |  |  |
| mb  | K      | mounting base; connected to cathode |  |  |

6. Ordering information

Table 3. Ordering information

| Type number  | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|--------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WN3S40200CBT | TO263        | WN3S40200CBTJ         | Reel           | 800                    | TO263d          | 17-Mar-2023        |

7. Marking

Table 4. Marking codes

| Type number  | Marking codes    |
|--------------|------------------|
| WN3S40200CBT | WN3S40<br>200CBT |

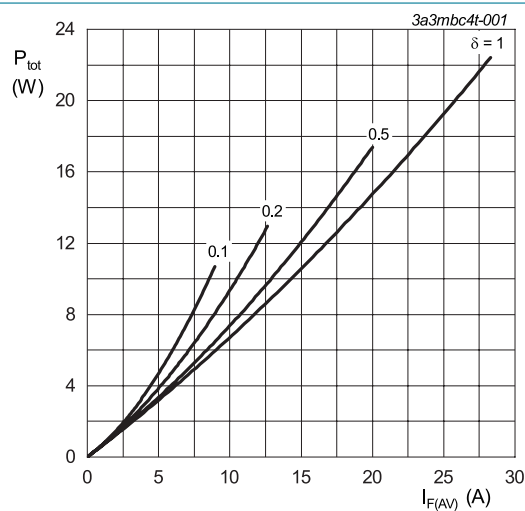
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

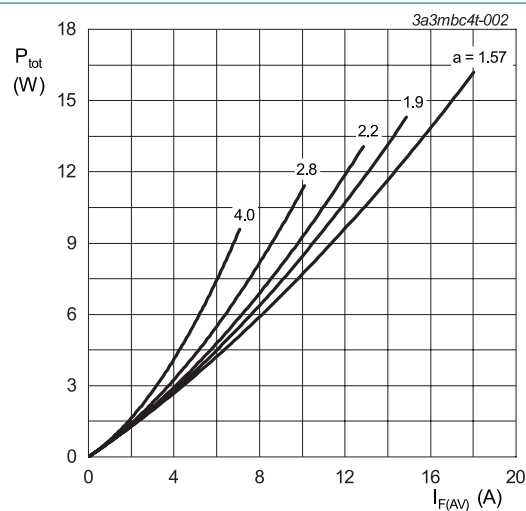
| Symbol      | Parameter                           | Conditions  | Notes | Values     | Unit               |
|-------------|-------------------------------------|---|-------|------------|--------------------|
| $V_{RRM}$   | repetitive peak reverse voltage     |   |       | 200        | V                  |
| $V_{RWM}$   | crest working reverse voltage       |   |       | 200        | V                  |
| $V_R$       | reverse voltage                     | DC  |       | 200        | V                  |
| $I_{F(AV)}$ | average forward current             | $\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 149\text{ }^{\circ}\text{C}$ ; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> |       | 20         | A                  |
| $I_{O(AV)}$ | average output current              | $\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 148\text{ }^{\circ}\text{C}$ ; both diodes conducting  |       | 40         | A                  |
| $I_{FSM}$   | non-repetitive peak forward current | $t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; sine-wave pulse; per diode; <a href="#">Fig. 4</a>                                       |       | 300        | A                  |
|             |                                     | $t_p = 8.3\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; sine-wave pulse; per diode  |       | 330        | A                  |
| $T_{stg}$   | storage temperature                 |   |       | -40 to 175 | $^{\circ}\text{C}$ |
| $T_j$       | junction temperature                |   | [1]   | -40 to 175 | $^{\circ}\text{C}$ |

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient:  $dP_{tot}/dT_j < 1/R_{th(j-a)}$



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$   
 $V_o = 0.605\text{ V}; R_s = 0.0066\text{ }\Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$   
 $V_o = 0.605\text{ V}; R_s = 0.0066\text{ }\Omega$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

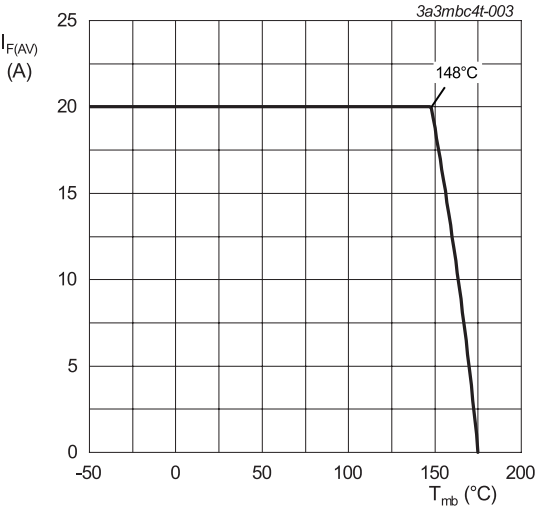


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

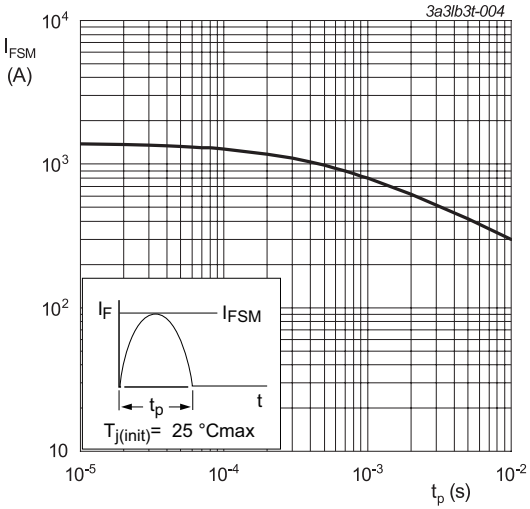


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter  | Conditions                        | Notes | Min | Typ | Max  | Unit |
|----------------|--|-----------------------------------|-------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base    | per diode; <a href="#">Fig. 5</a> |       | -   | -   | 1.56 | K/W  |
|                |  | both diodes conducting            |       | -   | -   | 0.76 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient free air | in free air                       |       | -   | 60  | -    | K/W  |

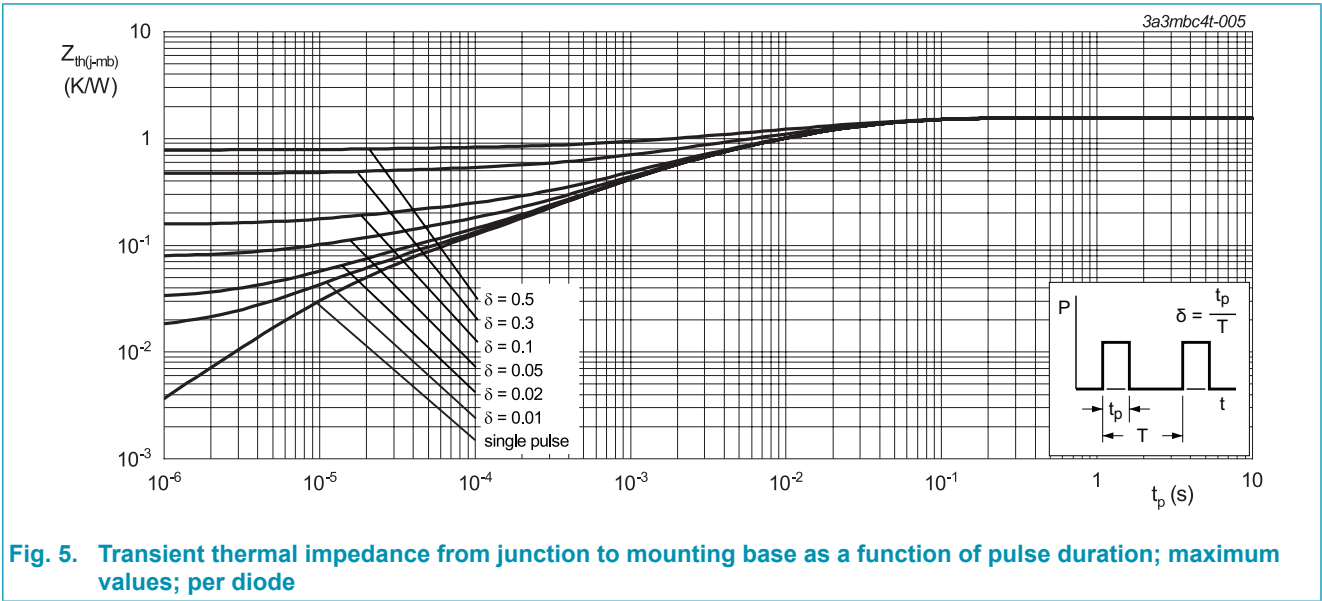
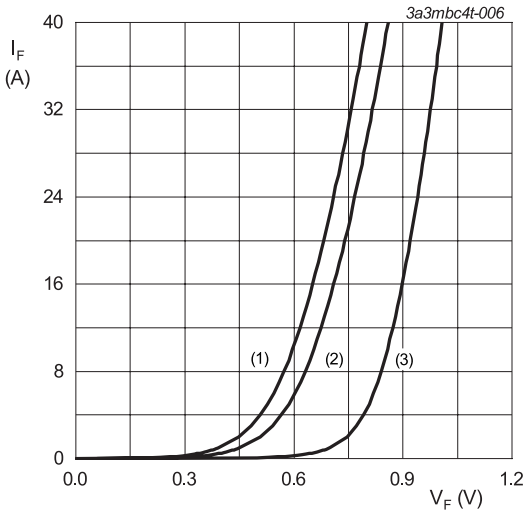


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

10. Characteristics

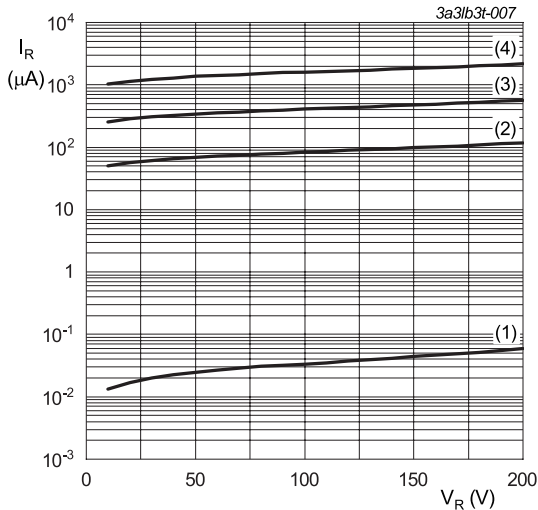
Table 7. Characteristics

| Symbol                 | Parameter       | Conditions   | Notes | Min | Typ  | Max  | Unit |
|------------------------|-----------------|--|-------|-----|------|------|------|
| Static characteristics |                 |  |       |     |      |      |      |
| V <sub>F</sub>         | forward voltage | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; Fig. 6   |       | -   | 0.87 | 0.92 | V    |
|                        |                 | I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; per diode          |       | -   | 0.75 | -    | V    |
|                        |                 | I <sub>F</sub> = 20 A; T <sub>j</sub> = 175 °C; per diode; Fig. 6  |       | -   | 0.69 | 0.74 | V    |
| I <sub>R</sub>         | reverse current | V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C; per diode; Fig. 7  |       | -   | 0.1  | 5    | μA   |
|                        |                 | V <sub>R</sub> = 200 V; T <sub>j</sub> = 125 °C; per diode; Fig. 7 |       | -   | 0.2  | -    | mA   |



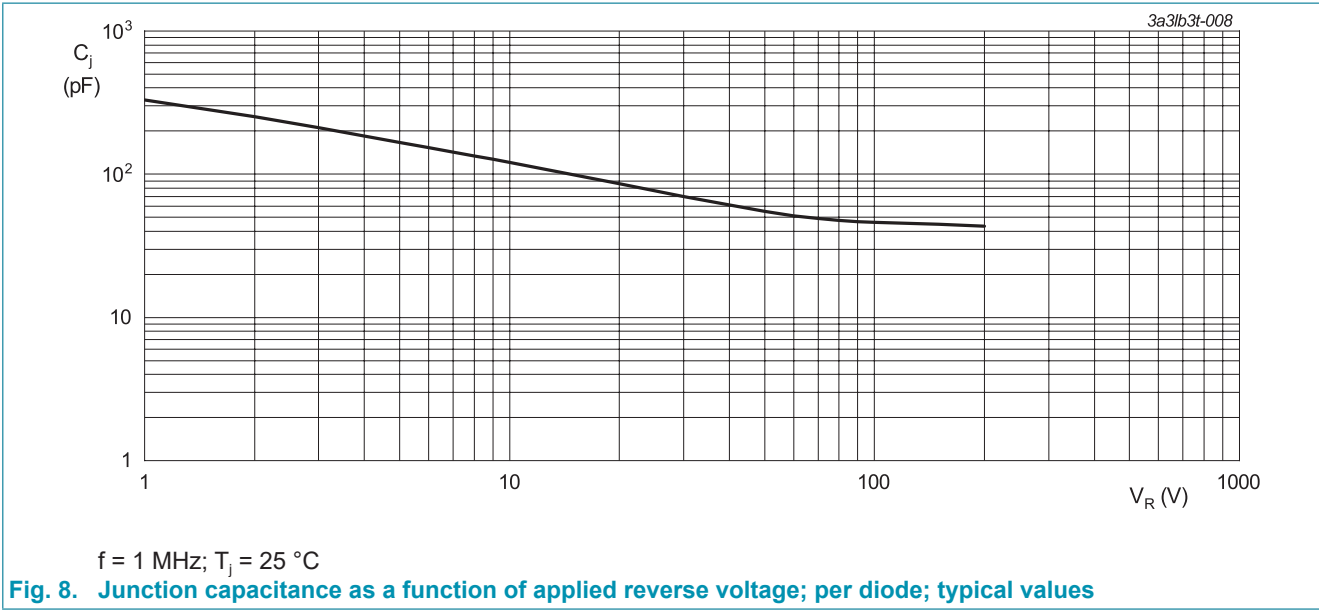
V<sub>o</sub> = 0.605 V; R<sub>s</sub> = 0.0066 Ω  
(1) T<sub>j</sub> = 175 °C; typical values  
(2) T<sub>j</sub> = 175 °C; maximum values  
(3) T<sub>j</sub> = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



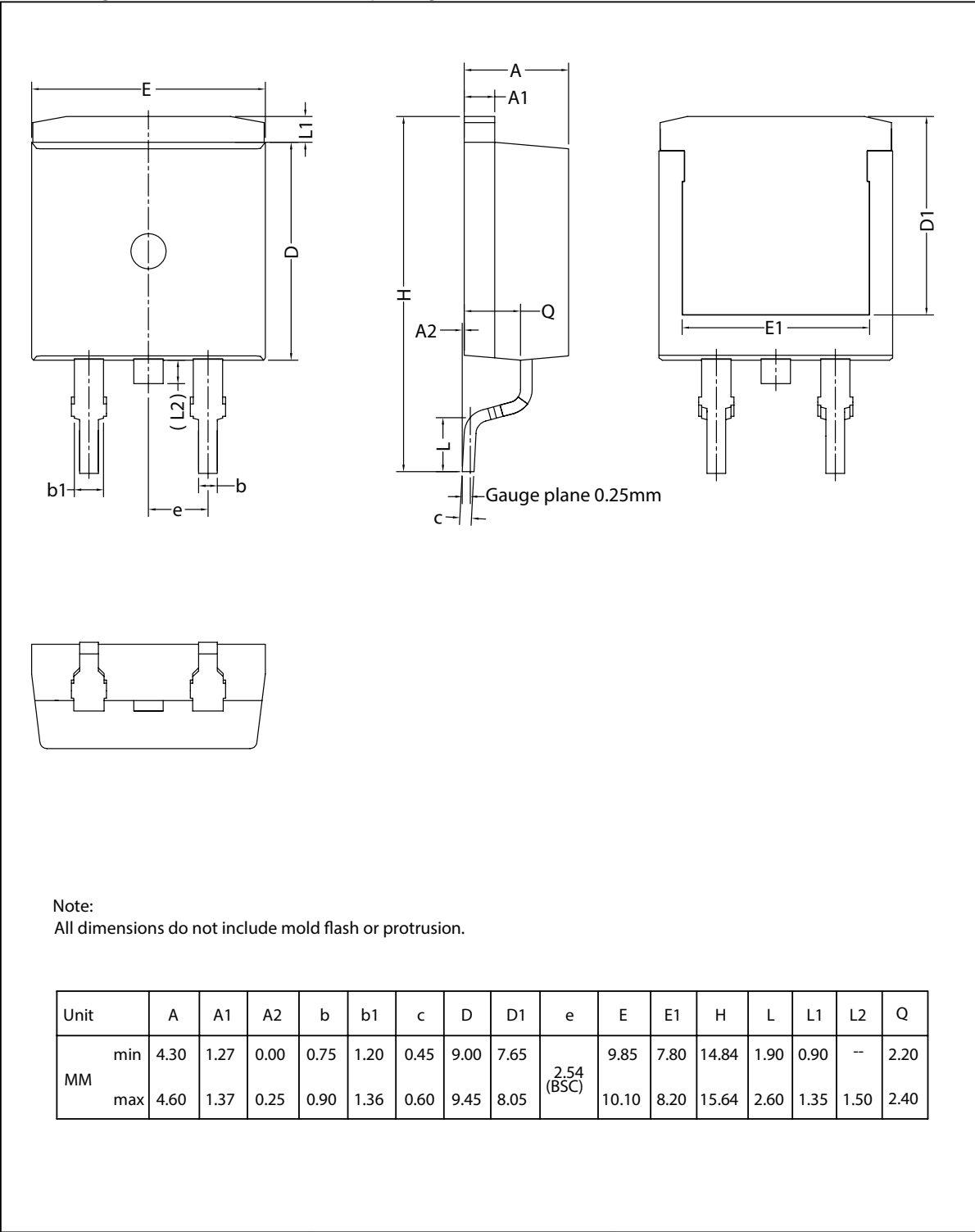
(1) T<sub>j</sub> = 25 °C; typical values  
(2) T<sub>j</sub> = 125 °C; typical values  
(3) T<sub>j</sub> = 150 °C; typical values  
(4) T<sub>j</sub> = 175 °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



11. Package outline

Plastic single-ended surface-mounted package (D2PAK); TO263





## 12. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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